

RIC7S113E4

RADIATION HARDENED HIGH AND LOW SIDE GATE DRIVER

Features

- Total dose capability to 100 kRads(Si)
- Floating channel designed for bootstrap operation
- Fully operational to +400V
- Tolerant to negative transient voltage
- dV/dt immune
- Gate drive supply range from 10 to 20V
- Undervoltage lockout for both channels
- Separate logic supply range from 5 to 20V
Logic and power ground $\pm 5V$ offset
- CMOS Schmitt-triggered inputs with pull-down
- Cycle by cycle edge-triggered shutdown logic
- Matched propagation delay for both channels
- Outputs in phase with inputs
- Hermetically Sealed
- Lightweight

Product Summary

V_{OFFSET}	400V max.
I_{O+/-}	2A / 2A
V_{OUT}	10 - 20V
t_{on/off} (typ.)	120 & 100 ns
Delay Matching(typ.)	5 ns

Description

The RIC7S113E4 is a high voltage, high speed power MOSFET and IGBT driver with independent high and low side referenced output channels. Proprietary HVIC and latch immune CMOS technologies enable ruggedized monolithic construction. Logic inputs are compatible with standard CMOS or LSTTL outputs. The output drivers feature a high pulse current buffer stage designed for minimum driver cross-conduction. Propagation delays are matched to simplify use in high frequency applications. The floating channel can be used to drive an N-channel power MOSFET or IGBT in the high side configuration which operates up to 400 volts.

Absolute Maximum Ratings

Absolute Maximum Ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The Thermal Resistance and Power Dissipation ratings are measured under board mounted and still air conditions.

Symbol	Parameter	Min.	Max.	Units
V _B	High Side Floating Supply Voltage	-0.5	V _S + 20	V
V _S	High Side Floating Supply Offset Voltage	—	400	
V _{HO}	High Side Floating Output Voltage	V _S - 0.5	V _B + 0.5	
V _{CC}	Low Side Fixed Supply Voltage	-0.5	20	
V _{LO}	Low Side Output Voltage	-0.5	V _{CC} + 0.5	
V _{DD}	Logic Supply Voltage	-0.5	V _{SS} + 20	
V _{SS}	Logic Supply Offset Voltage	V _{CC} - 20	V _{CC} + 0.5	
V _{IN}	Logic Input Voltage (HIN, LIN & SD)	V _{SS} - 0.5	V _{DD} + 0.5	
dV _S /dt	Allowable Offset Supply Voltage Transient (Figure 2)	—	50	V/ns
P _D	Package Power Dissipation @ T _{LEAD} ≤ +25°C	—	1.6	W
R _{thJC}	Thermal Resistance, Junction to Case	12 (Typ)	15.6	°C/W
R _{thJ-LEAD}	Thermal Resistance, Junction to Lead *	23 (Typ)	—	
R _{thJ-LID}	Thermal Resistance, Junction to Lid *	29 (Typ)	—	
T _J	Junction Temperature	-55	125	°C
T _S	Storage Temperature	-55	150	
T _L	Lead Temperature (Soldering, 10 seconds)	—	300	
	Weight	0.42(typical)		g

* Guaranteed by design, not tested

Recommended Operating Conditions

The Input/Output logic timing diagram is shown in Figure 1. The V_S and V_{SS} offset ratings are tested with all supplies biased at 15V differential.

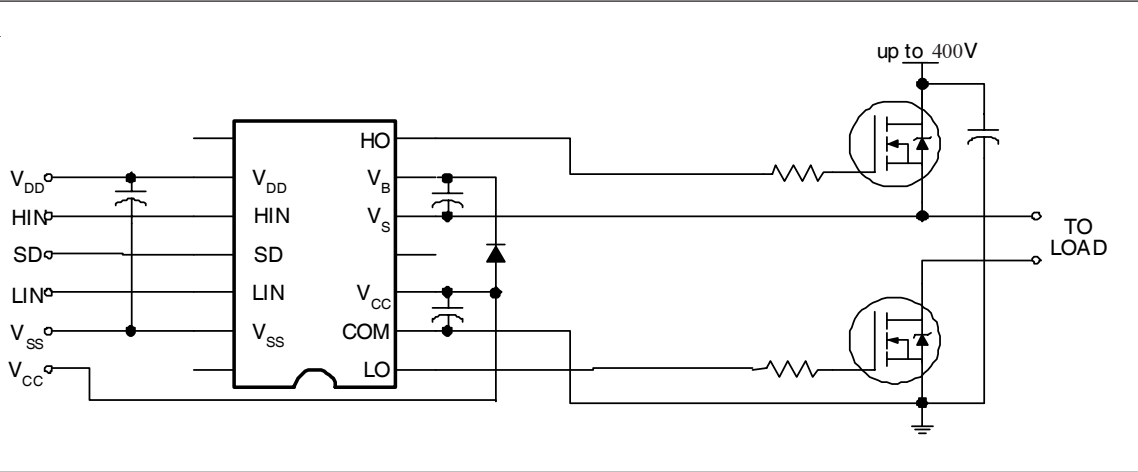
Symbol	Parameter	Min.	Max.	Units
V_B	High Side Floating Supply Absolute Voltage	$V_S + 10$	$V_S + 20$	V
V_S	High Side Floating Supply Offset Voltage	-4	400	
V_{HO}	High Side Floating Output Voltage	V_S	V_B	
V_{CC}	Low Side Fixed Supply Voltage	10	20	
V_{LO}	Low Side Output Voltage	0	V_{CC}	
V_{DD}	Logic Supply Voltage	$V_{SS} + 5$	$V_{SS} + 20$	
V_{SS}	Logic Supply Offset Voltage	-5	5	
V_{IN}	Logic Input Voltage (HIN, LIN & SD)	V_{SS}	V_{DD}	

Dynamic Electrical Characteristics

V_{BIAS} (V_{CC} , V_B , V_{DD}) = 15V, and V_{SS} = COM unless otherwise specified. The dynamic electrical characteristics are measured using the test circuit shown in Figure 3.

Symbol	Parameter	$T_j = 25^{\circ}C$			$T_j = -55 \text{ to } 125^{\circ}C$		Units	Test Conditions
		Min.	Typ.	Max.	Min.	Max.		
t_{on}	Turn-On Propagation Delay	—	120	150	—	260	ns	$V_S = 0V$
t_{off}	Turn-Off Propagation Delay	—	100	125	—	220		$V_S = 400V$
t_{sd}	Shutdown Propagation Delay	—	110	140	—	235		$V_S = 400V$
t_r	Turn-On Rise Time	—	25	35	—	50		$C_L = 1000pf$
t_f	Turn-Off Fall Time	—	17	25	—	40		$C_L = 1000pf$
MT	Delay Matching, HS & LS Turn-On/Off	—	5	20	—	—		$ t_{ton} - t_{ton} \text{ or } t_{toff} - t_{toff} $

Typical Connection



Static Electrical Characteristics

V_{BIAS} (V_{CC}, V_{BS}, V_{DD}) = 15V, unless otherwise specified. The V_{IN}, V_{TH} and I_{IN} parameters are referenced to V_{SS} and are applicable to all three logic input pins: HIN, LIN and SD. The V_O and I_O parameters are referenced to COM or V_S and are applicable to the respective output pins: HO or LO.

Symbol	Parameter	T _j = 25°C		T _j = -55 to 125°C		Units	Test Conditions
		Min.	Max.	Min.	Max.		
V _{IH}	Logic "1" Input Voltage	3.1	—	3.3	—	V	V _{DD} = 5V
		6.4	—	6.8	—		V _{DD} = 10V
		9.5	—	10	—		V _{DD} = 15V
		12.5	—	13.3	—		V _{DD} = 20V
V _{IL}	Logic "0" Input Voltage	—	1.6	—	1.6	V	V _{DD} = 5V
		—	3.8	—	3.6		V _{DD} = 10V
		—	6.0	—	5.7		V _{DD} = 15V
		—	8.3	—	7.9		V _{DD} = 20V
V _{OH}	High Level Output Voltage, V _{BIAS} - V _O	—	1.2	—	1.5	μA	V _{IN} = V _{IH} , I _O = 0A
V _{OL}	Low Level Output Voltage, V _O	—	0.1	—	0.1		V _{IN} = V _{IH} , I _O = 0A
I _{LK}	Offset Supply Leakage Current	—	50	—	250		V _B = V _S = 400V
I _{QBS}	Quiescent V _{BS} Supply Current	—	230	—	500		V _{IN} = 0V, or V _{DD}
I _{QCC}	Quiescent V _{CC} Supply Current	—	340	—	600		V _{IN} = 0V, or V _{DD}
I _{QDD}	Quiescent V _{DD} Supply Current	—	30	—	60		V _{IN} = 0V, or V _{DD}
I _{IN+}	Logic "1" Input Bias Current	—	40	—	70		V _{IN} = V _{DD}
I _{IN-}	Logic "0" Input Bias Current	—	1.0	—	10		V _{IN} = 0V
V _{BSUV+}	V _{BS} Supply Undervoltage Positive Going Threshold	7.5	9.7	—	—	V	
V _{BSUV-}	V _{BS} Supply Undervoltage Negative Going Threshold	7.0	9.4	—	—		
V _{CCUV+}	V _{CC} Supply Undervoltage Positive Going Threshold	7.4	9.6	—	—		
V _{CCUV-}	V _{CC} Supply Undervoltage Negative Going Threshold	7.0	9.4	—	—		
I _{O+}	Output High Short Circuit Pulsed Current *	2.0	—	—	—	A	V _O = 0V, V _{IN} = V _{DD} PW ≤ 10 μs
I _{O-}	Output Low Short Circuit Pulsed Current *	2.0	—	—	—		V _O = 15V, V _{IN} = 0V PW ≤ 10 μs

* Guaranteed by design, not tested

Radiation Performance

International Rectifier Radiation Hardened gate drivers are tested to verify their hardness capability. The hardness assurance program at International rectifier uses a Cobalt-60 (^{60}Co) source and heavy ion irradiation.

Every wafer shall be tested per MIL-STD-883, Method 1019, test condition A "Ionizing Radiation (Total Dose) Test Procedure".

Both pre- and post- irradiation performances are tested and specified using the same drive circuitry and test conditions to provide a direct comparison.

For Static Irradiation Test Conditions refer to Figure 7.

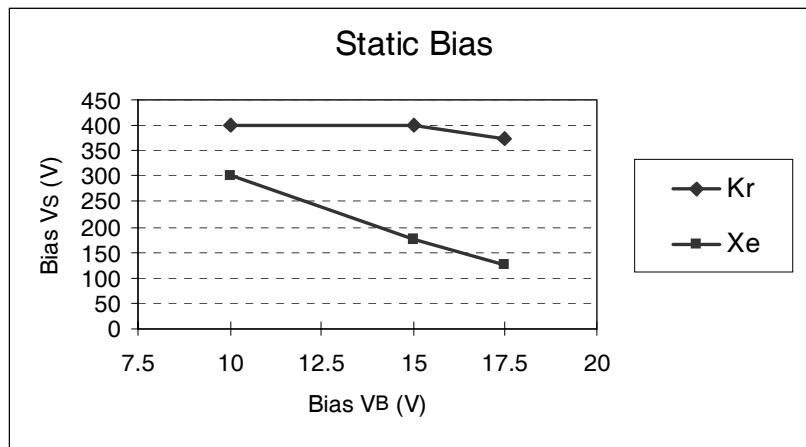
Static Electrical Characteristics		T _j = 25°C		Units	Test Conditions
Symbol	Parameter	100K Rads (Si)			
		Min	Max		
V _{IH}	Logic "1" Input Voltage	3.1	—	V	VDD = 5V
		6.4	—		VDD = 10V
		9.5	—		VDD = 15V
		12.5	—		VDD = 20V
V _{IL}	Logic "0" Input Voltage	—	1.6	V	VDD = 5V
		—	3.8		VDD = 10V
		—	6.0		VDD = 15V
		—	8.3		VDD = 20V
V _{OH}	High Level Output Voltage, V _{BIAS} - V _O	—	1.2		V _{IN} = V _{IH} , I _O = 0A
V _{OL}	Low Level Output Voltage, V _O	—	0.1		V _{IN} = V _{IH} , I _O = 0A
I _{LK}	Offset Supply Leakage Current	—	50	μA	V _B = V _S = 400V
I _{QBS}	Quiescent V _{BS} Supply Current	—	230		V _{IN} = 0V or VDD
I _{QCC}	Quiescent V _{CC} Supply Current	—	340		V _{IN} = 0V or VDD
I _{QDD}	Quiescent V _{DD} Supply Current	—	30		V _{IN} = 0V or VDD
I _{IN+}	Logic "1" Input Bias Current	—	40		V _{IN} = VDD
I _{IN-}	Logic "0" Input Bias Current	—	1.0		V _{IN} = 0V
V _{BSUV+}	V _{BS} Supply Undervoltage Positive Going Threshold	7.5	9.7	V	
V _{BSUV-}	V _{BS} Supply Undervoltage Negative Going Threshold	7.0	9.4		
V _{CCUV+}	V _{CC} Supply Undervoltage Positive Going Threshold	7.4	9.9		
V _{CCUV-}	V _{CC} Supply Undervoltage Negative Going Threshold	7.0	9.6		
I _{O+}	Output High Short Circuit Pulsed Current *	2.0	—	A	V _O = 0V, V _{IN} = VDD PW ≤ 10 μs
I _{O-}	Output Low Short Circuit Pulsed Current *	2.0	—		V _O = 15V, V _{IN} = 0V PW ≤ 10 μs

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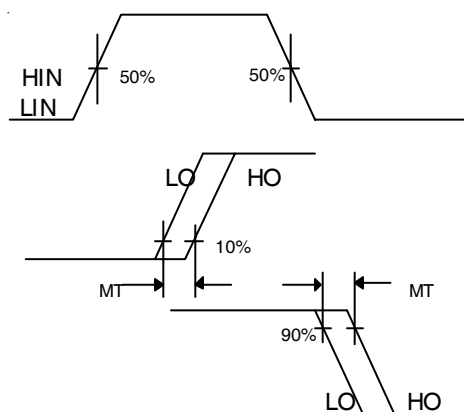
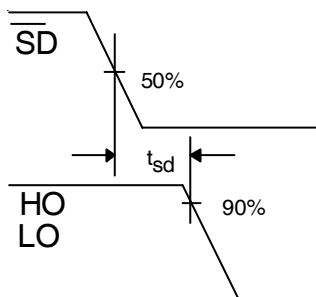
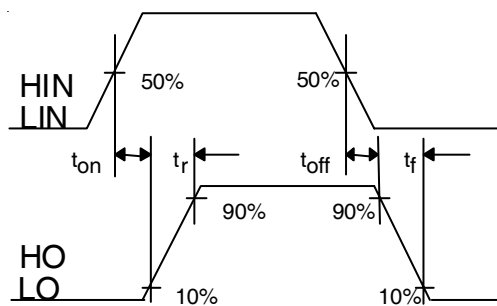
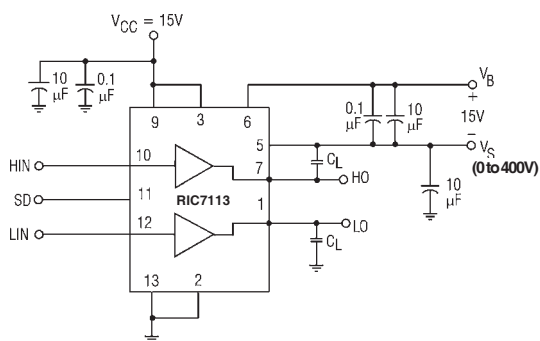
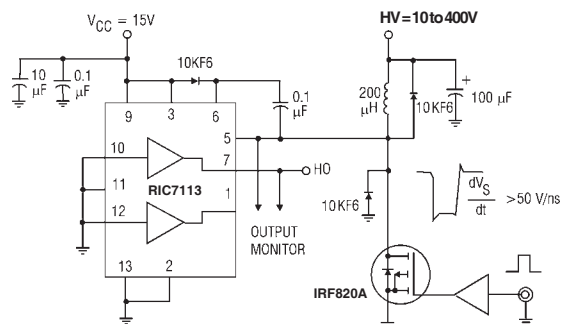
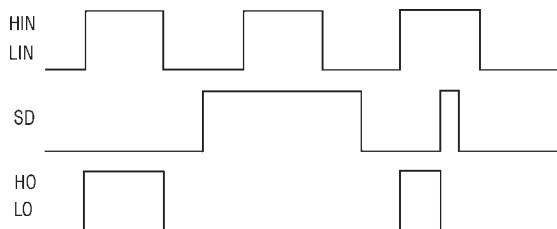
International Rectifier radiation hardened Gate Drivers have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization data is illustrated in Table and Curve below. For Static Bias Test Conditions refer to Figure 8.

Single Event Effect Safe Operating Area

Ion	LET (MeV/(mg/cm ²))	Energy (MeV)	Range (μm)	V _{CC} /V _{DD}	V _S (V)		
					V _B = 10V	V _B = 15V	V _B = 17.5V
Kr	27.2	1089	143	20V	400	400	375
Xe	50.4	1618	128.7	20V	300	175	125



International
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AN INFINEON TECHNOLOGIES COMPANY



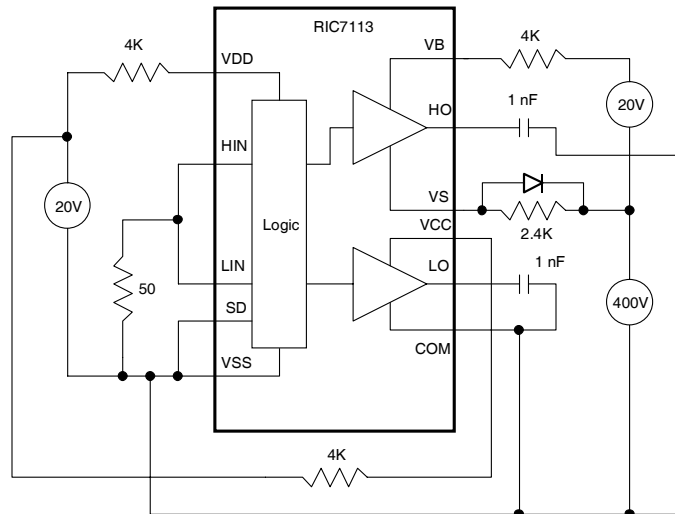


Figure 7. Static Bias Conditions for Total Ionizing Dose Test

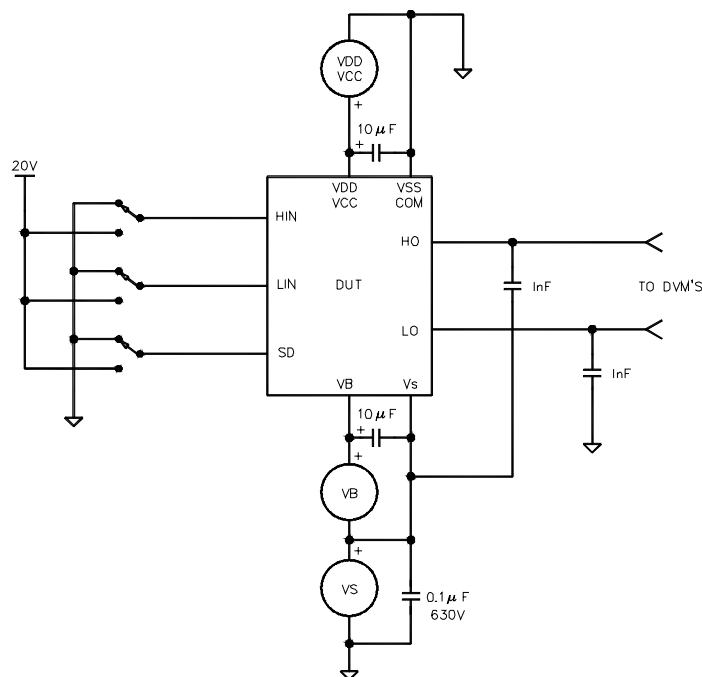
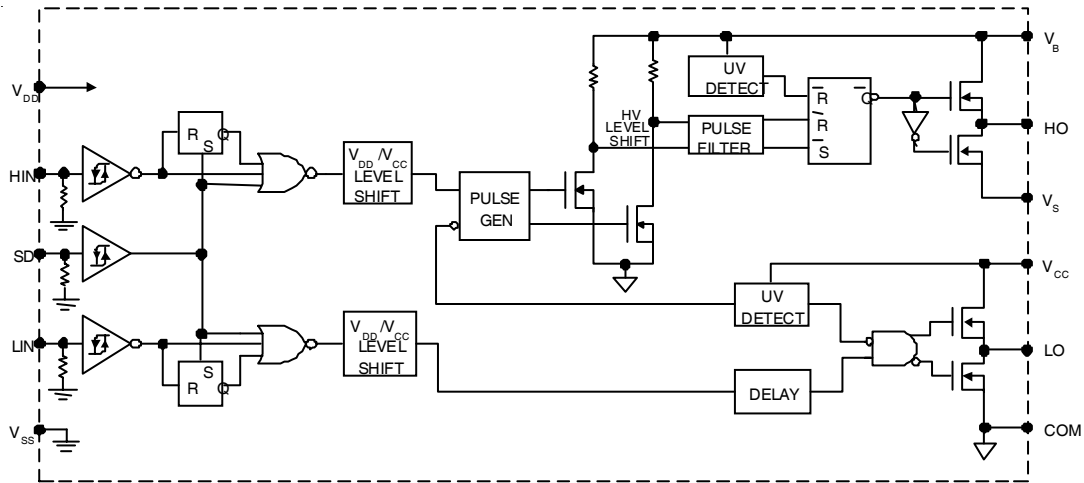


Figure 8. Static Bias Conditions for Single Event Effect Test

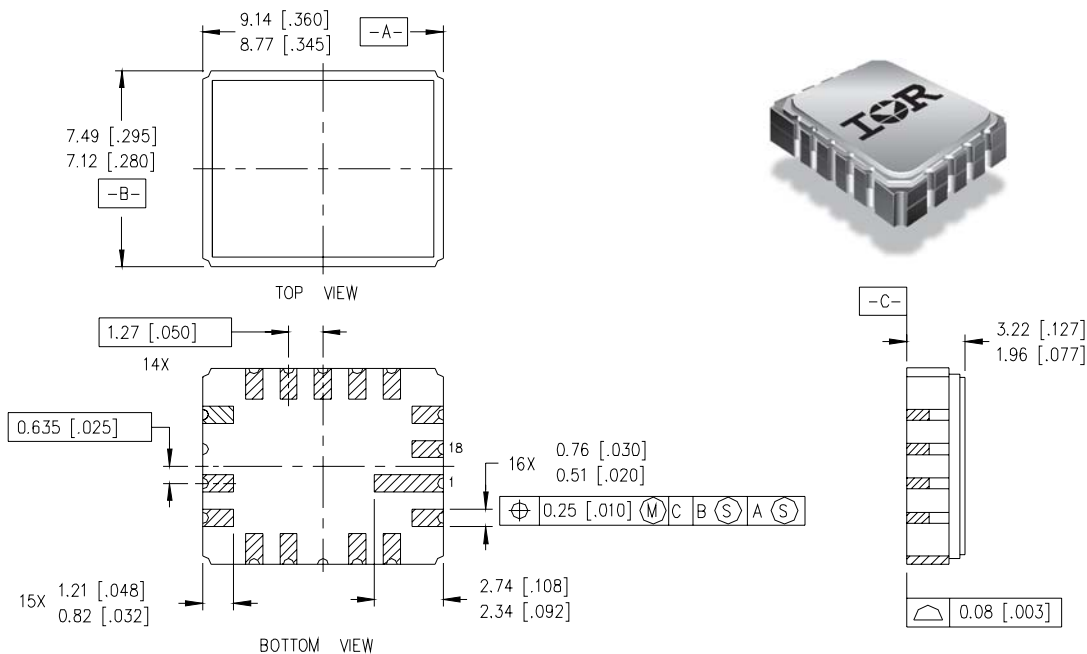
Functional Block Diagram



Lead Definitions

Symbol	Description
VDD	Logic supply
HIN	Logic input for high side gate driver output (HO), in phase
SD	Logic input for shutdown
LIN	Logic input for low side gate driver output (LO), in phase
VSS	Logic ground
VB	High side floating supply
HO	High side gate drive output
VS	High side floating supply return
VCC	Low side supply
LO	Low side gate drive output
COM	Low side return

Case Outline and Dimensions — Leadless Chip Carrier (LCC-18) Package



NOTES:

1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].

